L Number	Hits	Search Text	DB	Time stamp
1	5077	((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:32
2	42208	(polycrystalline or (p adj si)) near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:33
3	354399	irradiate or irradiating or irradiation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:34
4	255093	crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:35
5	23926	((a adj si) or (amorphous near2 silicon)) near (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:36
6	711816	laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
7	163809	anneal or annealing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
8	4110	((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
9	1995	(((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
10	1384	((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
11	1311	(((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
12	1154	((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:38

13	208	((((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:40
14	37776	active near2 matrix	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:40
15	162	(((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.)) and (active near2 matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:40
16	59309	channel near2 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:41
17	133	((((((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.)) and (active near2 matrix)) and (channel near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:41
18	17872	pixel near2 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:41
19	71	(((((((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.)) and (active near2 matrix)) and (channel near2 region)) and (pixel near2 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:41
-	4841	((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:32

-	0	quasi near2 strip near2 like near2 crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:35
-	2	quasi near2 strip near2 like	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:24
-	1188	polycrystalline same recrystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:25
-	0	(((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.) and (quasi near2 strip near2 like)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:25
-	7080	reformation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:25
-	83908	polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:21
-	6	reformation same polycrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:27
-	84120	polycrystalline or (p adj si adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:30
-	156387	anneal or annealing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:29
-	5374	(polycrystalline or (p adj si adj (layer or film))) same (anneal or annealing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:29
-	681508	laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:37
-	1662	laser same ((polycrystalline or (p adj si adj (layer or film))) same (anneal or annealing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:30
-	2666	lateral near2 growth	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:30
-	23	(laser same ((polycrystalline or (p adj si adj (layer or film))) same (anneal or annealing))) same (lateral near2 growth)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:30

-	5	(("200243222") or ("2002100637")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 21:39
-	202391	irradiate or irradiating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:34
-	89	(irradiate or irradiating) near (polycrystalline or (p adj si adj (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:21
-	5342	((438/30) or (438/128) or (438/149) or (438/166) or (438/488) or (438/489) or (438/491) or (438/795)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:17
-	26893	reform or reformation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:19
-	0	((irradiate or irradiating) near (polycrystalline or (p adj si adj (layer or film)))) same (reform or reformation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:19
-	0	((irradiate or irradiating) near (polycrystalline or (p adj si adj (layer or film)))) and (reform or reformation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:19
-	25571	pulse near laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:21
-	369	(pulse near laser) same (polycrystalline or (p adj si adj (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:22
-	177	((pulse near laser) same (polycrystalline or (p adj si adj (layer or film)))) and (irradiate or irradiating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:22
-	41017	(polycrystalline or (p adj si)) near2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:33
-	41	selective near irradiating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:34
-	1	((polycrystalline or (p adj si)) near2 (layer or film)) and (selective near irradiating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:32
-	17	(irradiate or irradiating) near (selective near irradiating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:35

-	0	((irradiate or irradiating) near ((polycrystalline or (p adj si)) near2 (layer or film))) and (quasi near like)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:35
-	104	(irradiate or irradiating) near ((polycrystalline or (p adj si)) near2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:40
-	101	sequential near lateral near solidification	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:41
-	55	(sequential near lateral near solidification) and ((polycrystalline or (p adj si)) near2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/11 22:42
-	103	quasi near like	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 10:20
-	2	(("20010026835") or ("20020031876")).PN.	USPAT; US-PGPUB	2004/05/14 16:03